Jae M Seo

List of Publications by Year
in descending order

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27	234	1040056	996975
papers	citations	9 h-index	15 g-index

27	27	27	134
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Atomic structure of the Si(5512)-2Ã—1 surface. Surface Science, 2007, 601, 1831-1835.	1.9	28
2	Atomic structure of Bi-dimer row selectively adsorbed on Si(5512)-2Ã—1 surface. Surface Science, 2004, 565, 14-26.	1.9	24
3	Cyclic transformation of one-dimensional structures during homoepitaxy of Si(5512)-2Ã—1. Surface Science, 2005, 583, 265-280.	1.9	22
4	Nucleation, growth, and deformation of one-dimensional Ge nanostructures on the Si(5512)-2Ã—1 surface. Surface Science, 2008, 602, 2563-2574.	1.9	17
5	Charge neutrality of quasi-free-standing monolayer graphene induced by the intercalated Sn layer. Journal Physics D: Applied Physics, 2016, 49, 135307.	2.8	16
6	Two distinct Sb-adsorption steps onSi(5512)â˜2Ã—1: Indiffusion followed by preferential adsorption. Physical Review B, 2007, 75, .	3.2	15
7	Doping modulation of quasi-free-standing monolayer graphene formed on SiC(0001) through Sn1-Ge intercalation. Carbon, 2019, 144, 549-556.	10.3	15
8	Origin of ambipolar graphene doping induced by the ordered Ge film intercalated on SiC(0001). Carbon, 2016, 108, 154-164.	10.3	14
9	Effects of two kinds of intercalated In films on quasi-free-standing monolayer graphene formed above SiC(0001). Carbon, 2020, 159, 229-235.	10.3	12
10	Bifunctional effects of the ordered Si atoms intercalated between quasi-free-standing epitaxial graphene and SiC(0001): graphene doping and substrate band bending. New Journal of Physics, 2015, 17, 083058.	2.9	9
11	Atomic structure of Si(5â€,5â€,12)-2Ã—1: Confirmation of the structural model having two kinds of chains through homoepitaxy at 550â€,Â°C. Journal of Vacuum Science & Technology B, 2007, 25, 1511.	1.3	8
12	Irreversible structural transformation of Si(1 1 4)-2 Ã— 1 induced by subsurface carbon. Surface Science, 2009, 603, 2312-2317.	1.9	7
13	Origin of ordered two-dimensional structure of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mtext>Si</mml:mtext><mml:mrow><mml:mo>(</mml:mo><mml:mrow><mml:mn>337</mml:mn></mml:mrow><mml:mo>)</mml:mo></mml:mrow></mml:mrow></mml:math> from<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"		

#	Article	IF	Citations
19	Metrological determination of a (6 9 17) facet on vicinalSi(5512)using STM. Physical Review B, 2006, 73, .	3.2	3
20	Synchrotron photoemission studies on reconstructed strained surfaces. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2011, 29, .	2.1	3
21	Origin of enhanced Ge interdiffusion at the initial stage of Ge deposition on Si(5 5 12)-2 Ã— 1: Tensile stress induced by substrate chain structures. Surface Science, 2012, 606, 744-748.	1.9	3
22	Initial CaF2 reactions on Si(1 1 4)-2 Ã— 1: Isolated silicides, faceting and partial CaF adsorption. Applied Surface Science, 2015, 357, 268-272.	6.1	3
23	Surface reconstruction switching induced by tensile stress of <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si1.gif" overflow="scroll"><mml:mrow><mml:msub><mml:mrow><mml:mi>D</mml:mi></mml:mrow><mml:mrow><mml:mi>B</mml:mi></mml:mrow> steps: From Ba/Si(0 0 1)-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" altimg="si14.gif" overflow="scroll"><mml:mrow><mml:mn>2</mml:mn><mml:mo>Ã—</mml:mo><mml:mn>3</mml:mn></mml:mrow></mml:math> to Ba/Si(0 0 1)-4A° of. Applied Surface Science, 2018, 439, 122-127.	6.1	2
24	Sn-induced 1D nanostructure formed on Si(5Â5Â12)-2â€²â€²Ã—â€²â€²1: Faceting followed by preferential adsorption. Surface Science, 2019, 688, 69-77.	1.9	1
25	Increased Stability of Subsurface C Induced by Ca on the C-Incorporated Si(001)-4Â°-off Substrate. Journal of the Korean Physical Society, 2020, 76, 991-1000.	0.7	1
26	Metrological orientation-confirmation of Si(hhk) using scanning tunneling microscopy. Applied Surface Science, 2011, 257, 4603-4607.	6.1	0
27	Growth mechanism of isolated indium nanowires formed on Si(5 5 12)-2 Ã— 1 templates. Journal of the Korean Physical Society, 2012, 61, 406-409.	0.7	0